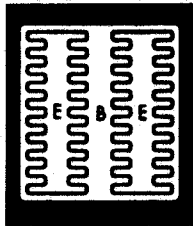


CHIP NUMBER

267



.106"
(2.69mm)

.098"
(2.49mm)

Base: .010" x .082" (0.25mm x 2.08mm)
Emitter: .009" x .074" (0.23mm x 1.88mm)

PNP EPITAXIAL PLANAR POWER TRANSISTOR* (FORMERLY 67)

CONTACT METALLIZATION

Base and emitter: > 30,000 Å Aluminum

Collector: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .220" Diameter (5.59mm)

Thickness: .010" (0.25mm)

BeO PEDESTAL

Size: .142" x .178" (3.61mm x 4.52mm)

Thickness: .028" (0.71mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the chip be eutectically mounted with gold silicon preform 98/2%.
- 8 mil (0.203mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 267 in a TO-3 or equivalent case:

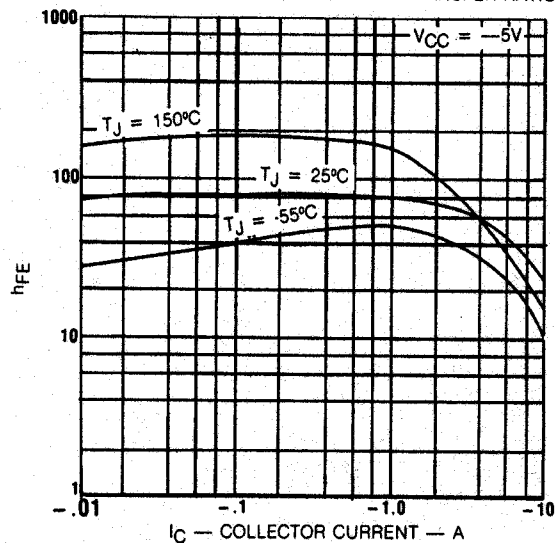
V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 60V	<0.5V	3A	0.3A	>10	8A	5V
> 80V	<0.5V	3A	0.3A	>10	8A	5V
>100V	<0.5V	3A	0.3A	>10	8A	5V
>120V	<0.5V	3A	0.3A	>10	8A	5V
* >150V	<0.5V	2A	0.2A	> 5	5A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	C _{OBO}	θ _{JC}
> 60V	70V	>5V	25MHz	<200pF	<1.5°C/W
> 80V	90V	>5V	25MHz	<200pF	<1.5°C/W
>100V	110V	>5V	25MHz	<200pF	<1.5°C/W
>120V	130V	>5V	25MHz	<200pF	<1.5°C/W
>150V	160V	>5V	25MHz	<200pF	<1.5°C/W

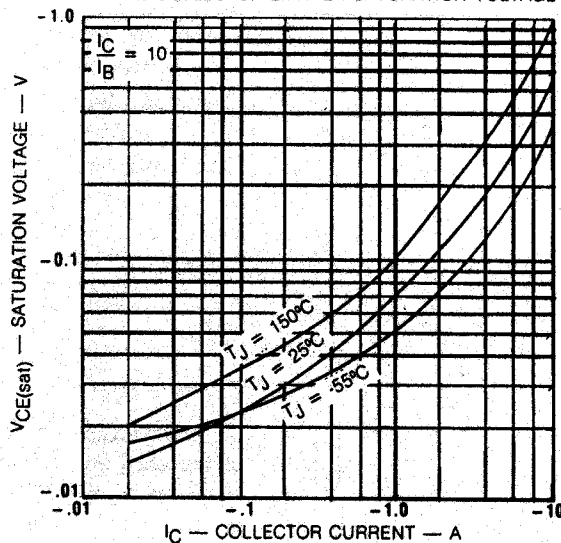
TYPICAL DEVICE TYPES: 2N5871, 2N5872, 2N3789 - 2N3792, 2N4907 - 2N4909, SDT3801 - SDT3807, 2N5738

*h_{FE} available at I_C = 2.5A, V_{CE} = 5.0V, >10

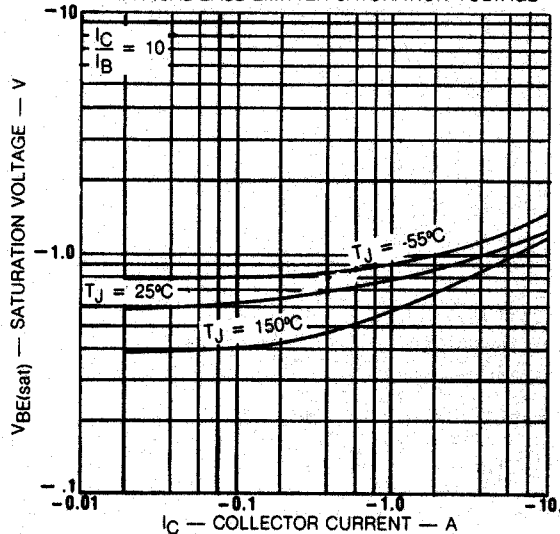
TYPICAL STATIC FORWARD CURRENT TRANSFER RATIO



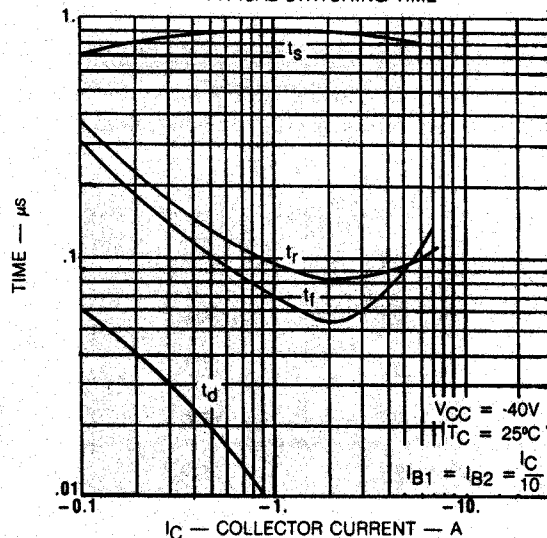
TYPICAL COLLECTOR EMITTER SATURATION VOLTAGE



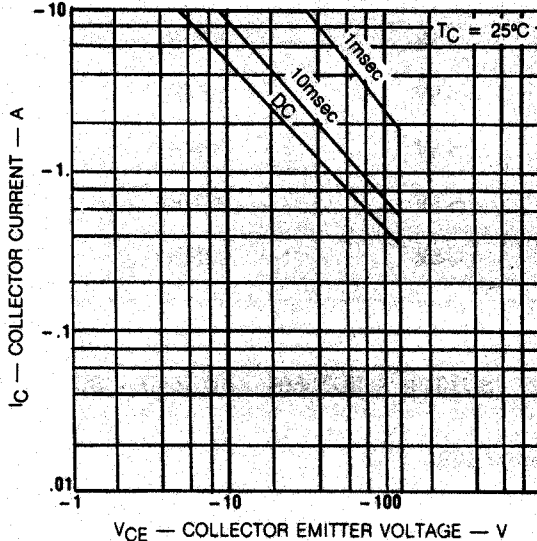
TYPICAL BASE EMITTER SATURATION VOLTAGE



TYPICAL SWITCHING TIME



MAXIMUM OPERATING CONDITIONS



NOTE:
PERFORMANCE CURVES
REPRESENT LOW TO
MIDDLE CEO VOLTAGE
RANGE OF THIS PRODUCT